

TS5A23157

SCDS165D-MAY 2004-REVISED MAY 2008

10

9

<u>8</u> V₊

7 NC2

6

NC1

V+

NC2

COM₂

8

7

6

COM1

COM2

NC1

DGS PACKAGE

(TOP VIEW)

RSE PACKAGE (TOP VIEW)

COM1

10 9

:5

IN2

2

3

4

IN1

NO1

GND

NO2

IN2

IN1

NO1

GND

NO2

DUAL 10- Ω SPDT ANALOG SWITCH

FEATURES

www.ti.com

- Specified Break-Before-Make Switching
- Low ON-State Resistance (10 Ω)
- Control Inputs Are 5-V Tolerant
- Low Charge Injection
- Excellent ON-Resistance Matching
- Low Total Harmonic Distortion
- 1.8-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

APPLICATIONS

- Sample-and-Hold Circuits
- Battery-Powered Equipment
- Audio and Video Signal Routing
- Communication Circuits

DESCRIPTION/ORDERING INFORMATION

The TS5A23157 is a dual single-pole double-throw (SPDT) analog switch designed to operate from 1.65 V to 5.5 V. This device can handle both digital and analog signals. Signals up to 5.5 V (peak) can be transmitted in either direction.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾	(2)	ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
–40°C to 85°C	VSSOP (MSOP-10) – DGS	Tape and reel	TS5A23157DGSR	JBR
-40 C 10 85 C	QFN – RSE	Tape and reel	TS5A23157RSER	JB_

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(3) RSE: The actual top-side marking has one additional character that designates the assembly/test site.

FUNCTION TABLE

INPUT IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
н	OFF	ON



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SCDS165D-MAY 2004-REVISED MAY 2008

SUMMARY OF CHARACTERISTICS					
Configuration	2:1 Multiplexer/Demultiplexer (2 \times SPDT)				
Number of channels	2				
ON-state resistance (ron)	10 Ω				
ON-state resistance match between channels (Δr_{on})	0.15 Ω				
ON-state resistance flatness (r _{on(flat)})	4 Ω				
Turn-on/turn-off time (t _{ON} /t _{OFF})	5.7 ns/3.8 ns				
Break-before-make time (t _{BBM})	0.5 ns				
Charge injection (Q _C)	7 pC				
Bandwidth (BW)	220 MHz				
OFF isolation (OSIO)	-65 dB at 10 MHz				
Crosstalk 9XTALK)	–66 dB at 10 MHz				
Total harmo nic distortion (THD)	0.01%				
Leakage current (I _{COM(OFF)} /I _{NC(OFF)})	±1 μΑ				
Package options	10-pin DGS and RSE				

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V+	Supply voltage range ⁽²⁾		-0.5	6.5	V
V _{NC} V _{NO} V _{COM}	Analog voltage range ⁽²⁾⁽³⁾⁽⁴⁾		-0.5	V ₊ + 0.5	V
I _{I/OK}	Analog port diode current	V_{NC} , V_{NO} , V_{COM} < 0 or V_{NC} , V_{NO} , V_{COM} > V_{+}		±50	mA
I _{NC} I _{NO} I _{COM}	On-state switch current	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{+}		±50	mA
V _{IN}	Digital input voltage range ⁽²⁾⁽³⁾		-0.5	6.5	V
I _{IK}	Digital input clamp current	V _{IN} < 0		-50	mA
	Continuous current through V_+ or GND			±100	mA
0		DGS package		56.5	0000
θ_{JA}	Package thermal impedance ⁽⁵⁾	RSE package		243	°C/W
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(4) This value is limited to 5.5 V maximum.

(5) The package thermal impedance is calculated in accordance with JESD 51-7.



www.ti.com

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY

 V_{\star} = 4.5 V to 5.5 V, T_{A} = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V.	MIN	TYP ⁽¹⁾	MAX	UNIT
Analog Switch						r.		ľ	
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		V+	V
ON-state resistance	r _{on}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -30 \text{ mA},$	Switch ON, See Figure 10	Full	4.5 V			10	Ω
ON-state resistance match between channels	Δr _{on}	V_{NO} or V_{NC} = 3.15 V, I_{COM} = -30 mA,	Switch ON, See Figure 10	25°C	4.5 V		0.15		Ω
ON-state resistance flatness	r _{on(flat)}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -30 \text{ mA},$	Switch ON, See Figure 10	25°C	4.5 V		4		Ω
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0$ to V_+ ,	Switch OFF,	25°C	5.5 V	-1	0.05	1	μA
OFF leakage current	I _{NO(OFF)}	$V_{COM} = 0$ to V_+ ,	See Figure 11	Full	5.5 V	-1		1	
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0$ to V_+ ,	Switch ON,	25°C	5.5 V	-0.1		0.1	μA
ON leakage current	I _{NO(ON)}	V _{COM} = Open,	See Figure 11	Full	5.5 V	-1		1	
COM		V _{NC} or V _{NO} = Open,	Switch ON,	25°C	5.5 V	-0.1		0.1	
ON leakage current	ICOM(ON)	$V_{COM} = 0$ to V_+ ,	See Figure 11	Full	5.5 V	-1		1	μA
Digital Inputs (IN12, IN	N2) ⁽²⁾								
Input logic high	V _{IH}			Full		$V_{+} \times 0.7$			V
Input logic low	V _{IL}			Full				$\begin{array}{c} V_{+} \\ \times 0.3 \end{array}$	V
Input lookago ourront				25°C		-1	0.05	1	
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 5.5 V or 0		Full	5.5 V	-1		1	μA

(1)

 $T_A = 25^{\circ}C$ All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004. (2)

www.ti.com

INSTRUMENTS

Texas

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (continued)

 V_{+} = 4.5 V to 5.5 V, T_{A} = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDI	TIONS	TA	V ₊	MIN TYP ⁽¹) MAX	UNIT
Dynamic				- H				
Turn-on time	t _{ON}	$\label{eq:VNC} \begin{array}{l} V_{NC} = GND \text{ and } V_{NO} = V_{+} \\ \text{or} \\ V_{NC} = V_{+} \text{ and } V_{NO} = GND, \end{array}$	$C_{L} = 50 \text{ pF},$	Full	4.5 V to 5.5 V	1.7	5.7	ns
Turn-off time	t _{OFF}	$\label{eq:VNC} \begin{array}{l} V_{NC} = GND \text{ and } V_{NO} = V_{+} \\ \text{or} \\ V_{NC} = V_{+} \text{ and } V_{NO} = GND, \end{array}$	C _L = 50 pF,	Full	4.5 V to 5.5 V	0.8	3.8	ns
Break-before-make time	t _{BBM}	$\label{eq:VNC} \begin{split} V_{\text{NC}} &= V_{\text{NO}} = V_{\text{+}}/2, \\ R_{\text{L}} &= 50 \ \Omega, \end{split}$	C _L = 35 pF, See Figure 14	Full	4.5 V to 5.5 V	0.5		ns
Charge injection	Q _C	$\label{eq:VNC} \begin{split} V_{\text{NC}} &= V_{\text{NO}} = V_{\text{+}}/2, \\ R_{\text{L}} &= 50 \ \Omega, \end{split}$	See Figure 18	25°C	5 V	-	7	рС
NC, NO OFF capacitance	$\begin{array}{c} C_{NC(OFF)},\\ C_{NO(OFF)} \end{array}$	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch OFF, See Figure 12	25°C	5 V	5.	5	pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND,	Switch ON, See Figure 12	25°C	5 V	17.	5	pF
COM ON capacitance	C _{COM(ON)}	$V_{COM} = V_+ \text{ or GND},$	Switch ON, See Figure 12	25°C	5 V	17.	5	pF
Digital input capacitance	C _{IN}	$V_{IN} = V_{+}$ or GND,	See Figure 12	25°C	5 V	2.8	3	pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 15	25°C	4.5 V	220)	MHz
OFF isolation	O _{ISO}	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 10 \ MHz, \end{array} $	Switch OFF, See Figure 16	25°C	4.5 V	-65	5	dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega,$ f = 10 MHz,	Switch ON, See Figure 17	25°C	4.5 V	-60	6	dB
Total harmonic distortion	THD		f = 600 Hz to 20 kHz, See Figure 19	25°C	4.5 V	0.0	1	%
Supply				- ·	· · · · · ·			
Positive supply	I+	V _{IN} = V ₊ or GND,	Switch ON or OFF	25°C	5.5 V		1	μA
current			UFF	Full			10	· .
Change in supply current	ΔI_+	$V_{\rm IN} = V_+ - 0.6 \ V$		Full	5.5 V		500	μΑ

4

Copyright © 2004–2008, Texas Instruments Incorporated



www.ti.com

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY

 V_{\star} = 3 V to 3.6 V, T_{A} = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V+	MIN	TYP ⁽¹⁾	MAX	UNIT
Analog Switch	I.								
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		V+	V
ON-state resistance	r _{on}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -24 \text{ mA},$	Switch ON, See Figure 10	Full	3 V			18	Ω
ON-state resistance match between channels	Δr _{on}	V_{NO} or V_{NC} = 2.1 V, I_{COM} = -24 mA,	Switch ON, See Figure 10	25°C	3 V		0.2		Ω
ON-state resistance flatness	r _{on(flat)}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -24 \text{ mA},$	Switch ON, See Figure 12	25°C	3 V		9		Ω
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V_{NC} or $V_{NO} = 0$ to V_+ , $V_{COM} = 0$ to V_+ ,	Switch OFF, See Figure 11	25°C Full	3.6 V	-1 -1	0.05	1	μA
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	V_{NC} or $V_{NO} = 0$ to V_+ , $V_{COM} = Open$,	Switch ON, See Figure 11	25°C Full	3.6 V	-0.1 -1		0.1	μΑ
COM ON leakage current	I _{COM(ON)}	V_{NC} or V_{NO} = Open, V_{COM} = 0 to V_{+} ,	Switch ON, See Figure 11	25°C Full	3.6 V	-0.1 -1		0.1	μΑ
Digital Inputs (IN12, I	N2) ⁽²⁾								
Input logic high	V _{IH}			Full		V ₊ × 0.7			V
Input logic low	V _{IL}			Full				$\begin{array}{c} V_{\text{+}} \\ \times 0.3 \end{array}$	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 5.5 V or 0		25°C Full	3.6 V	-1 -1	0.05	1	μA
Dynamic									
Turn-on time	t _{ON}	V_{NC} = GND and V_{NO} = V ₊ or V_{NC} = V ₊ and V_{NO} = GND,	$R_L = 500 \Omega,$ $C_L = 50 pF,$ See Figure 13	Full	3 V to 3.6 V	2.5		7.6	ns
Turn-off time	t _{OFF}	V_{NC} = GND and V_{NO} = V ₊ or V_{NC} = V ₊ and V_{NO} = GND,	$R_{L} = 500 \Omega,$ $C_{L} = 50 \text{ pF},$ See Figure 13	Full	3 V to 3.6 V	1.5		5.3	ns
Break-before-make time	t _{BBM}	$\label{eq:VNC} \begin{split} V_{NC} &= V_{NO} = V_{+}/2, \\ R_{L} &= 50 \ \Omega, \end{split}$	C _L = 35 pF, See Figure 14	Full	3 V to 3.6 V	0.5			ns
Charge injection	Q _C	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ CL = 0.1 \ nF, \end{array} $	See Figure 18	25°C	3.3 V		3		рС
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 15	25°C	3 V		220		MHz
OFF isolation	O _{ISO}	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 10 \ MHz, \end{array} $	Switch OFF, See Figure 16	25°C	3 V		-65		dB
Crosstalk	X _{TALK}	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 10 \ MHz, \end{array} $	Switch ON, See Figure 17	25°C	3 V		-66		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 600 Hz to 20 kHz, See Figure 19	25°C	3 V		0.015		%
Supply									
Positive supply current	I+	$V_{IN} = V_{+} \text{ or GND},$	Switch ON or OFF	25°C Full	3.6 V			1 10	μΑ
Change in supply current	ΔI_+	$V_{IN} = V_{+} - 0.6 V$		Full	3.6 V			500	μΑ

(1) T_A = 25°C
 (2) All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

NSTRUMENTS

ÈXAS

www.ti.com

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V.	MIN	TYP ⁽¹⁾	MAX	UNIT
Analog Switch	1			1	1 1				
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		V+	V
ON-state resistance	r _{on}	$\begin{array}{l} 0 \leq V_{NO} \text{ or } V_{NC} \leq V_{+}, \\ I_{COM} = -8 \text{ mA}, \end{array}$	Switch ON, See Figure 10	Full	2.3 V			45	Ω
ON-state resistance match between channels	∆r _{on}	$\label{eq:VNO} \begin{array}{l} V_{NO} \text{ or } V_{NC} = 1.6 \text{ V}, \\ I_{COM} = -8 \text{ mA}, \end{array}$	Switch ON, See Figure 10	25°C	2.3 V		0.5		Ω
ON-state resistance flatness	r _{on(flat)}	$\begin{array}{l} 0 \leq V_{NO} \text{ or } V_{NC} \leq V_{+}, \\ I_{COM} = -8 \text{ mA}, \end{array}$	Switch ON, See Figure 10	25°C	2.3 V		27		Ω
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}		Switch OFF, See Figure 11	25°C Full	2.7 V	-1 -1	0.05	1	μΑ
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	V_{NC} or $V_{NO} = 0$ to V_+ , $V_{COM} = Open$,	Switch ON, See Figure 11	25°C Full	2.7 V	-0.1 -1		0.1 1	μΑ
COM ON leakage current	I _{COM(ON)}	V_{NC} or V_{NO} = Open, V_{COM} = 0 to V_+ ,	Switch ON, See Figure 11	25°C Full	2.7 V	-0.1 -1		0.1 1	μΑ
Digital Inputs (IN12, IN	12) ⁽²⁾								
Input logic high	V _{IH}			Full		$V_{+} \times 0.7$			V
Input logic low	V _{IL}			Full				$\begin{array}{c} V_{+} \\ \times 0.3 \end{array}$	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 5.5 V or 0		25°C Full	2.7 V	-1 -1	0.05	1	μΑ
Dynamic									
Turn-on time	t _{ON}	$\label{eq:VNC} \begin{array}{l} V_{NC} = GND \text{ and } V_{NO} = V_{+} \\ \text{or} \\ V_{NC} = V_{+} \text{ and } V_{NO} = GND, \end{array}$	C _L = 50 pF,	Full	2.3 V to 2.7 V	3.5		14	ns
Turn-off time	t _{OFF}		$C_{L} = 50 \text{ pF},$	Full	2.3 V to 2.7 V	2		7.5	ns
Break-before-make time	t _{BBM}	$\label{eq:VNC} \begin{split} V_{\text{NC}} &= V_{\text{NO}} = V_{\text{+}}/2, \\ R_{\text{L}} &= 50 \ \Omega, \end{split}$	C _L = 35 pF, See Figure 14	Full	2.3 V to 2.7 V	0.5			ns
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 15	25°C	2.3 V		220		MHz
OFF isolation	O _{ISO}	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 10 \ MHz, \end{array} $	Switch OFF, See Figure 16	25°C	2.3 V		-65		dB
Crosstalk	X _{TALK}	$ \begin{array}{l} R_{L} = 50 \ \Omega, \\ f = 10 \ MHz, \end{array} $	Switch ON, See Figure 17	25°C	2.3 V		-66		dB
Total harmonic distortion	THD		f = 600 Hz to 20 kHz, See Figure 19	25°C	2.3 V		0.025		%
Supply	1	1			<u>г </u>				
Positive supply current	I+	$V_{IN} = V_{+}$ or GND,	Switch ON or OFF	25°C Full	2.7 V			1 10	μA
Change in supply current	ΔI+	$V_{IN} = V_{+} - 0.6 V$		Full	2.7 V			500	μΑ

6

(1) $T_A = 25^{\circ}C$ (2) All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



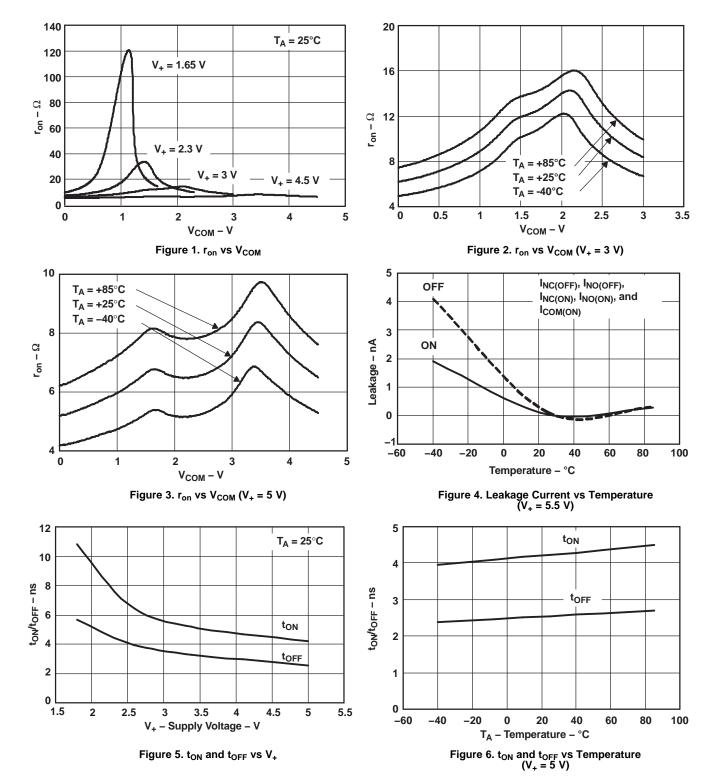
www.ti.com

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY

V₊ = 1.65 V to 1.95 V, T_A = -40° C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V.	MIN	TYP ⁽¹⁾	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		V+	V
ON-state resistance	r _{on}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -4 \text{ mA},$	Switch ON, See Figure 10	Full	1.65 V			140	Ω
ON-state resistance match between channels	Δr _{on}	V_{NO} or V_{NC} = 1.15 V, I_{COM} = -4 mA,	Switch ON, See Figure 10	25°C	1.65 V		1		Ω
ON-state resistance flatness	r _{on(flat)}	$0 \le V_{NO} \text{ or } V_{NC} \le V_+,$ $I_{COM} = -4 \text{ mA},$	Switch ON, See Figure 10	25°C	1.65 V		110		Ω
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V_{NC} or $V_{NO} = 0$ to V_+ , $V_{COM} = 0$ to V_+ ,	Switch OFF, See Figure 11	25°C Full	1.95 V	-1 -1	0.05	1	μΑ
NC, NO ON leakage current	I _{NC(ON)} , I _{NO(ON)}	V_{NC} or $V_{NO} = 0$ to V_+ , $V_{COM} = Open$,	Switch ON, See Figure 11	25°C Full	1.95 V	-0.1 -1		0.1 1	μA
COM ON leakage current	I _{COM(ON)}	V_{NC} or V_{NO} = Open, V_{COM} = 0 to V_+ ,	Switch ON, See Figure 11	25°C Full	1.95 V	-0.1 -1		0.1 1	μA
Digital Inputs (IN12, IN	2) ⁽²⁾								
Input logic high	V _{IH}			Full		V ₊ × 0.75			V
Input logic low	V _{IL}			Full				V ₊ × 0.25	V
Input leakage current	$I_{\rm IH},I_{\rm IL}$	V _{IN} = 5.5 V or 0		25°C Full	1.95 V	-1 -1	0.05	1	μΑ
Dynamic					I	I			
Turn-on time	t _{ON}	V_{NC} = GND and V_{NO} = V ₊ or V_{NC} = V ₊ and V_{NO} = GND,	$C_{1} = 50 \text{ pF},$	Full	1.65 V to 1.95 V	7		24	ns
Turn-off time	t _{OFF}	V_{NC} = GND and V_{NO} = V ₊ or V_{NC} = V ₊ and V_{NO} = GND,	C _L = 50 pF,	Full	1.65 V to 1.95 V	3		13	ns
Break-before-make time	t _{BBM}		C _L = 35 pF, See Figure 14	Full	1.65 V to 1.95 V	0.5			ns
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 15	25°C	1.8 V		220		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega,$ f = 10 MHz,	Switch OFF, See Figure 16	25°C	1.8 V		-60		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega,$ f = 10 MHz,	Switch ON, See Figure 17	25°C	1.8 V		-66		dB
Total harmonic distortion	THD		f = 600 Hz to 20 kHz, See Figure 19	25°C	1.8 V		0.015		%
Supply									
Positive supply current	I+	$V_{IN} = V_{+}$ or GND,	Switch ON or OFF	25°C Full	1.95 V			1 10	μA
Change in supply current	ΔI ₊	$V_{IN} = V_{+} - 0.6 V$		Full	1.95 V			500	μA

(1) T_A = 25°C
 (2) All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



TYPICAL CHARACTERISTICS

www.ti.com

INSTRUMENTS

Texas





SCDS165D-MAY 2004-REVISED MAY 2008



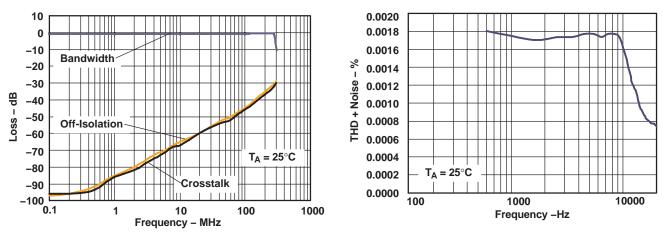
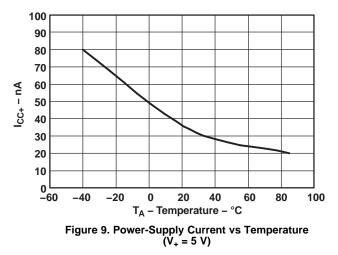


Figure 7. Frequency Response (V₊ = 3 V)

Figure 8. Total Harmonic Distortion (THD) vs Frequency ($V_{+} = 3 V$)



TEXAS INSTRUMENTS

www.ti.com

SCDS165D-MAY 2004-REVISED MAY 2008

PIN NO.	NAME	DESCRIPTION
1	IN1	Digital control to connect COM to NO or NC
2	NO1	Normally open
3	GND	Digital ground
4	NO2	Normally open
5	IN2	Digital control to connect COM to NO or NC
6	COM2	Common
7	NC2	Normally closed
8	V+	Power supply
9	NC1	Normally closed
10	COM1	Common

PIN DESCRIPTION

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NC}	Voltage at NC
V _{NO}	Voltage at NO
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
∆r _{on}	Difference of r _{on} between channels
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NC(OFF)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
I _{NC(ON)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) being open
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) being open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (NO to COM or NC to COM) in the ON state and the output (NC or NO) being open
V _{IH}	Minimum input voltage for logic high for the control input (IN)
V _{IL}	Minimum input voltage for logic low for the control input (IN)
V _{IN}	Voltage at IN
I _{IH} , I _{IL}	Leakage current measured at IN
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning ON.
t _{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning OFF.
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
Q _C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulombs) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_O$, C_L is the load capacitance and ΔV_O is the change in analog output voltage.
C _{NC(OFF)}	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
C _{NO(OFF)}	Capacitance at the NO port when the corresponding channel (NC to COM) is OFF
C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NC to COM) is ON
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
C _{IN}	Capacitance of IN
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state. OFF isolation, $O_{ISO} = 20 \text{ LOG}$ (V_{NC}/V_{COM}) dB, V_{COM} is the input and V_{NC} is the output.



TS5A23157

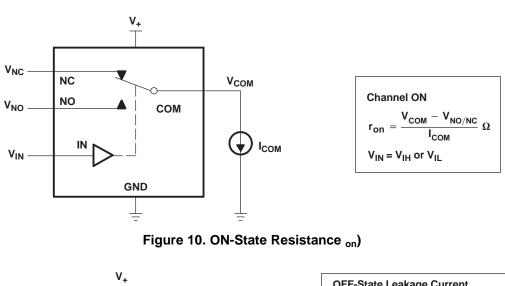
SCDS165D-MAY 2004-REVISED MAY 2008

www.ti.com

PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured at a specific frequency and in dB. Crosstalk, $X_{TALK} = 20 \log (V_{NC1}/V_{NO1})$, V_{NO1} is the input and V_{NC1} is the output.
BW	Bandwidth of the switch. This is the frequency where the gain of an ON channel is -3 dB below the dc gain. Gain is measured from the equation, 20 log (V _{NC} /V _{COM}) dB, where V _{NC} is the output and V _{COM} is the input.
I+	Static power-supply current with the control (IN) pin at V ₊ or GND
ΔI_+	This is the increase in I ₊ for each control (IN) input that is at the specified voltage, rather than at V ₊ or GND.





PARAMETER MEASUREMENT INFORMATION

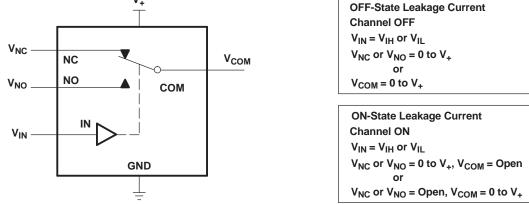
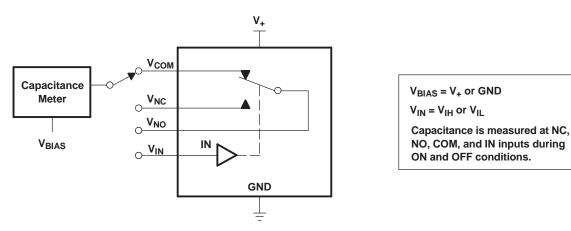
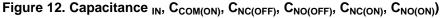


Figure 11. ON- and OFF-State Leakage Current (I_{COM(ON)}, I_{NC(OFF)}, I_{NO(OFF)}, I_{NC(ON)}, I_{NO(ON)})







www.ti.com

PARAMETER MEASUREMENT INFORMATION (continued)

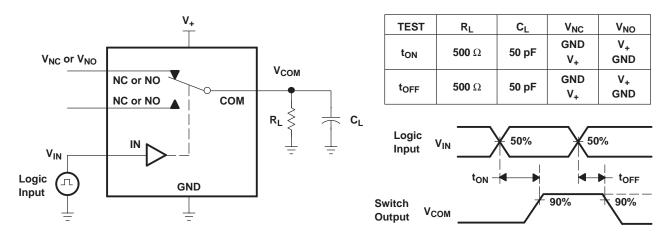


Figure 13. Turn-On (t_{ON}) and Turn-Off (t_{OFF}) Time

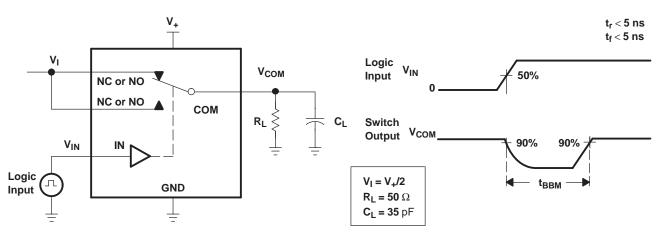


Figure 14. Break-Before-Make (t_{BBM}) Time

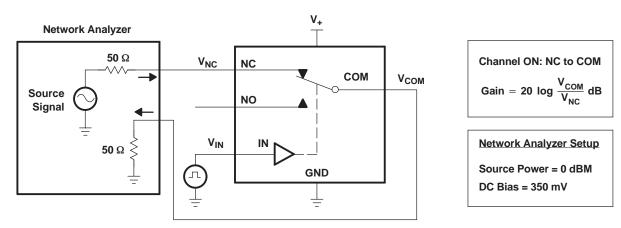


Figure 15. Frequency Response (BW)



PARAMETER MEASUREMENT INFORMATION (continued)

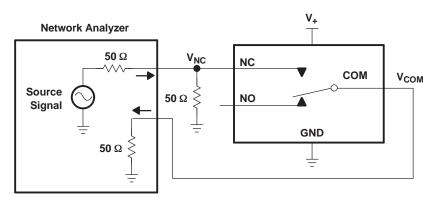
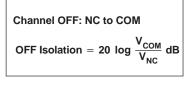
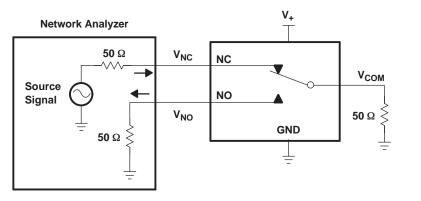


Figure 16. OFF Isolation (O_{ISO})



<u>Network Analyzer Setup</u> Source Power = 0 dBM DC Bias = 350 mV



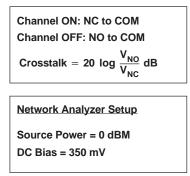
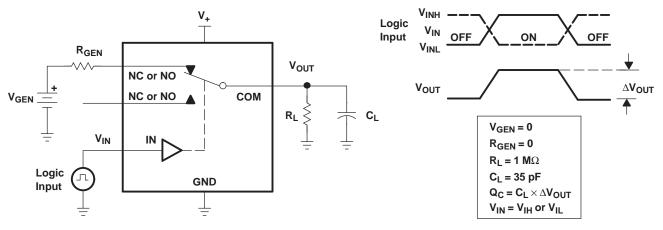


Figure 17. Crosstalk (X_{TALK)}









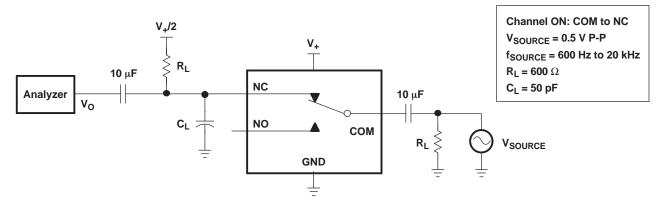


Figure 19. Total Harmonic Distortion (THD)



11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package Qty	Eco Plan	Lead/Ball Finish		Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		હાપ્ર	(2)		(3)		(4)	
TS5A23157DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157DGSRE4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157DGST	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157DGSTE4	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157DGSTG4	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBR	Samples
TS5A23157RSER	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBO	Samples
TS5A23157RSERG4	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JBO	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



11-Apr-2013

⁽⁴⁾ Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TS5A23157 :

Automotive: TS5A23157-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*A	Il dimensions are nominal												
	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	TS5A23157DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
	TS5A23157RSER	UQFN	RSE	10	3000	179.0	8.4	1.75	2.25	0.65	4.0	8.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

19-Nov-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A23157DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A23157RSER	UQFN	RSE	10	3000	203.0	203.0	35.0

DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE



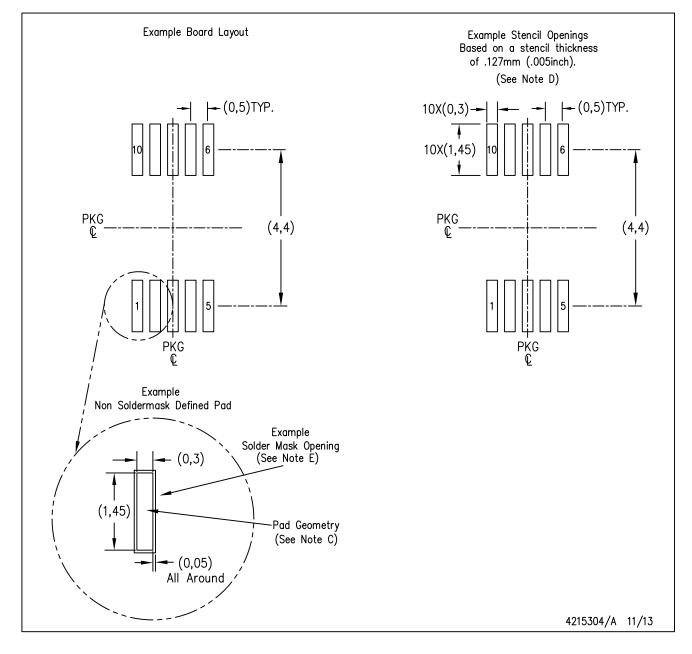
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



DGS (S-PDSO-G10)

PLASTIC SMALL OUTLINE PACKAGE

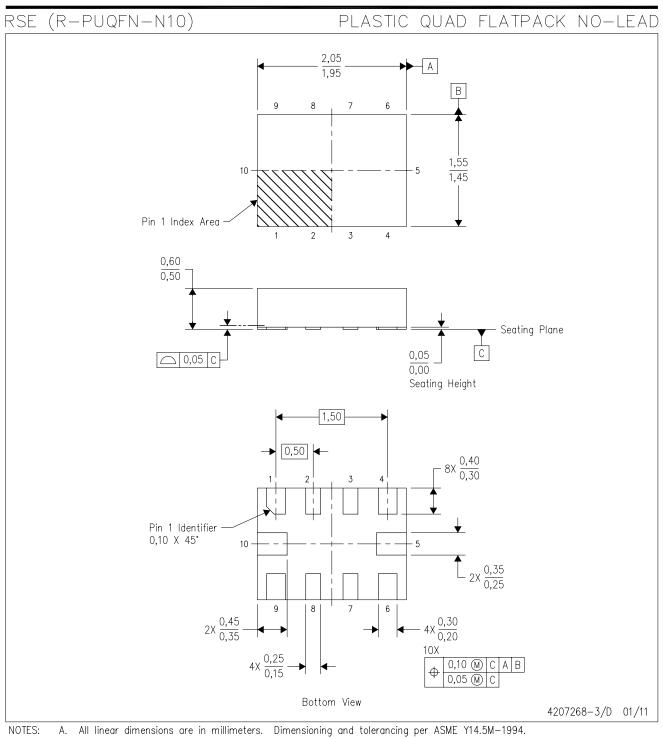


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

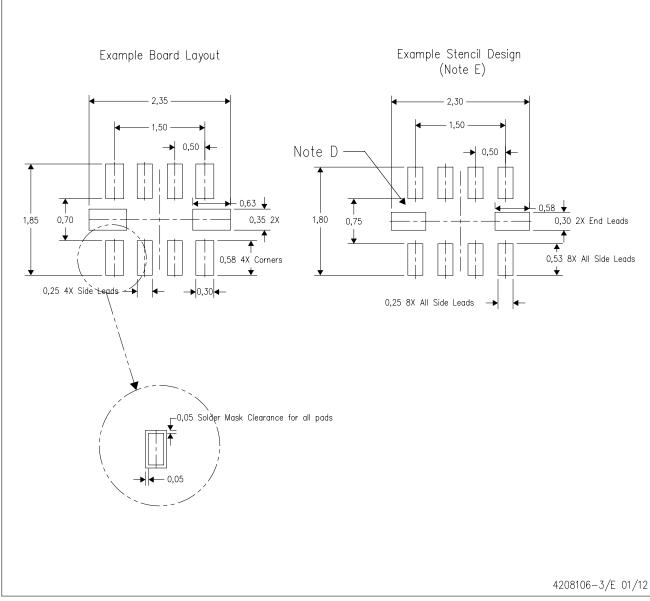


- B. This drawing is subject to change without notice.
 C. QFN (Quad Flatpack No-Lead) package configuration.
 D. This package complies to JEDEC MO-288 variation UEFD.



RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ectivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2013, Texas Instruments Incorporated

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Texas Instruments: TS5A23157DGSTE4